Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
-12V	18mΩ@ V_{GS} = -4.5V	-7.2A
	22mΩ@ V_{GS} = -2.5V	-6.5A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power Management Functions

Mechanical Data

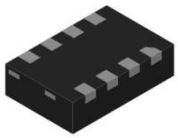
- Case: V-DFN3020-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.011 grams (Approximate)

V-DFN3020-8

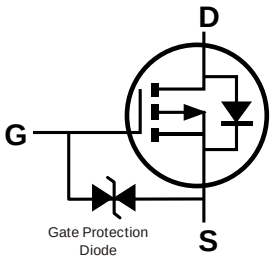




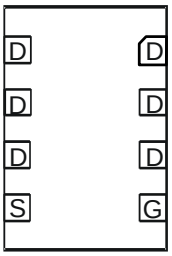
Top View



Bottom View



Equivalent Circuit



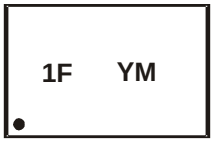
Bottom View
Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1022UWS-7	V-DFN3020-8	3000/Tape & Reel
DMP1022UWS-13	V-DFN3020-8	10000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



1F = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: F = 2018)
M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	F	G	H	I	J	K	L	M	N	O	P

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings – P-CHANNEL MOSFET (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-12	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	-7.2 -5.3	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-9.4 -7.6	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	-1.8	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-60	A
Avalanche Current (Note 7) L = 0.1mH			I_{AS}	-13	A
Avalanche Energy (Note 7) L = 0.1mH			E_{AS}	9	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	135	°C/W
	t<10s		78	
Total Power Dissipation (Note 6)		P_D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	90	°C/W
	t<10s		52	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	15.6	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics – P-CHANNEL MOSFET (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-12	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -10V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.35	—	-1	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	12	18	mΩ	V_{GS} = -4.5V, I_D = -9A
			15	22		V_{GS} = -2.5V, I_D = -8.5A
			23	28		V_{GS} = -1.8V, I_D = -7.5A
Diode Forward Voltage	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0V, I_S = -8A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	2847	—	pF	V_{DS} = -4V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	808	—		
Reverse Transfer Capacitance	C_{rss}	—	731	—		
Gate Resistance	R_g	—	9	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	30	—	nC	V_{GS} = -5V, V_{DS} = -4V, I_D = -10A
Total Gate Charge	Q_g	—	27	—		V_{GS} = -4.5V, V_{DS} = -4V, I_D = -10A
Gate-Source Charge	Q_{gs}	—	4.1	—		
Gate-Drain Charge	Q_{gd}	—	6.4	—		
Turn-On Delay Time	$t_{D(ON)}$	—	20	—	ns	V_{DS} = -4V, V_{GS} = -4.5V, R_g = 1Ω, I_D = -9.8A
Turn-On Rise Time	t_R	—	28	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	117	—		
Turn-Off Fall Time	t_F	—	93	—		
Bodyy Diode Reverse Recovery Time	t_{RR}	—	28	—	ns	I_S = -9.8A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	13	—	nC	

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

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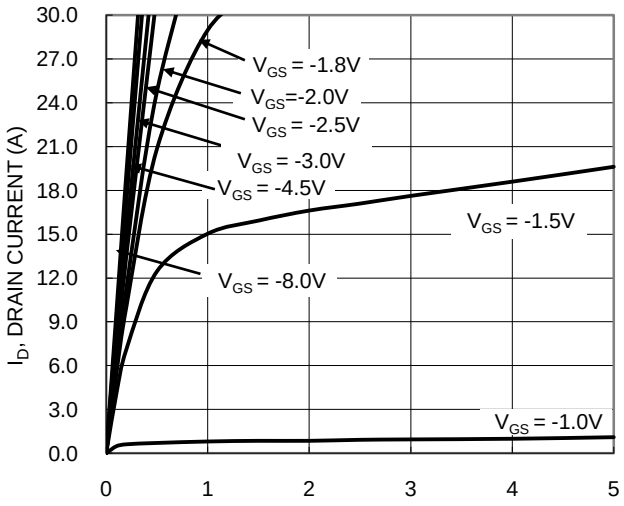


Figure 1. Typical Output Characteristic

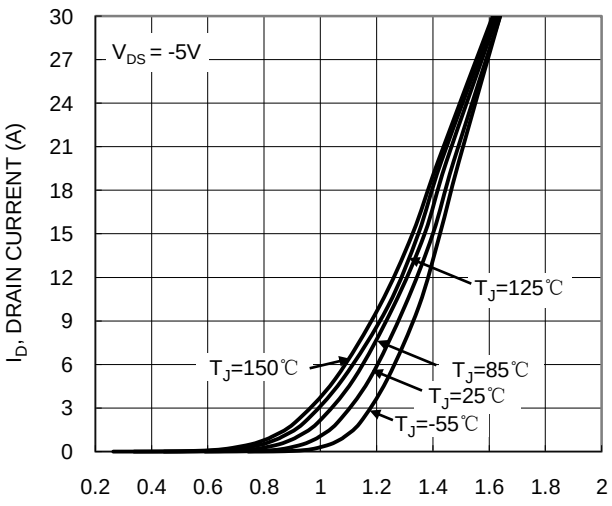


Figure 2. Typical Transfer Characteristic

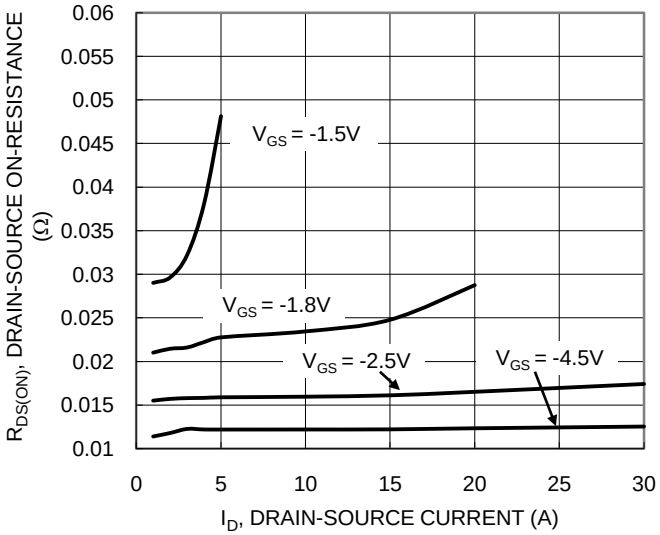


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

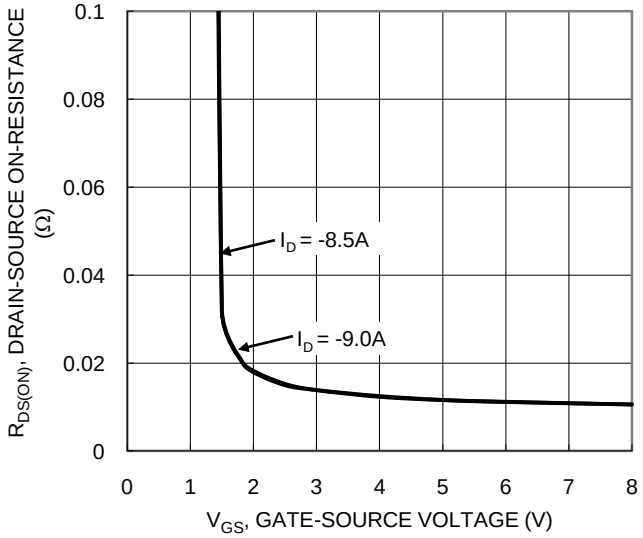


Figure 4. Typical Transfer Characteristic

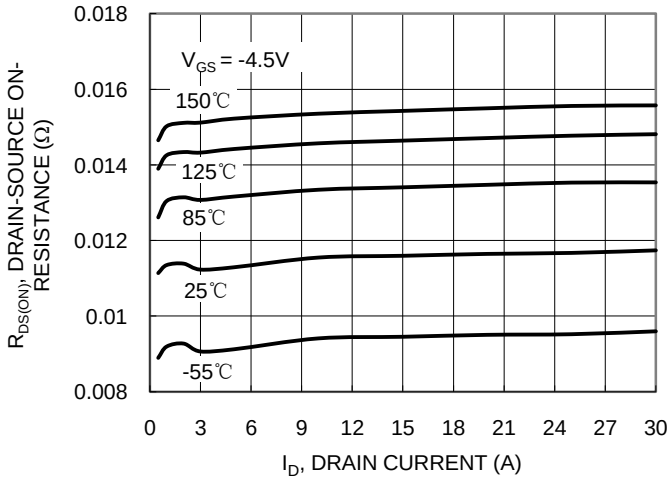


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

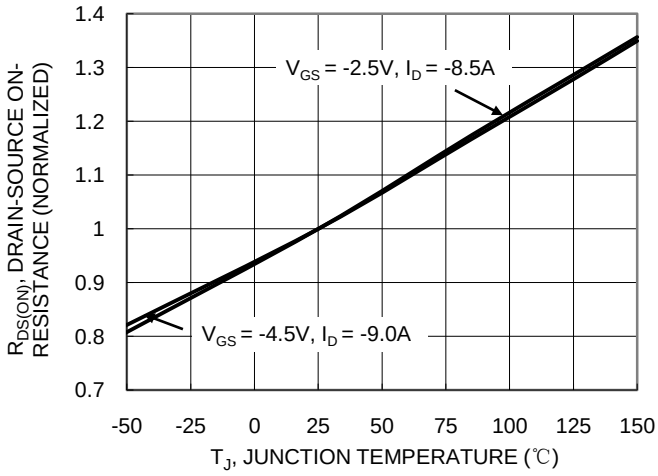


Figure 6. On-Resistance Variation with Temperature

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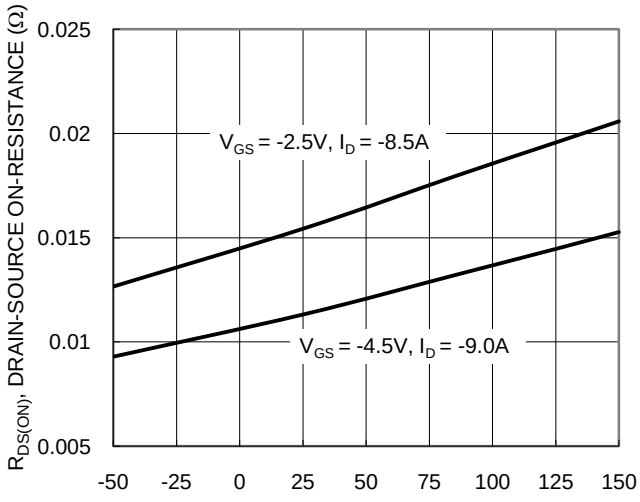


Figure 7. On-Resistance Variation with Temperature

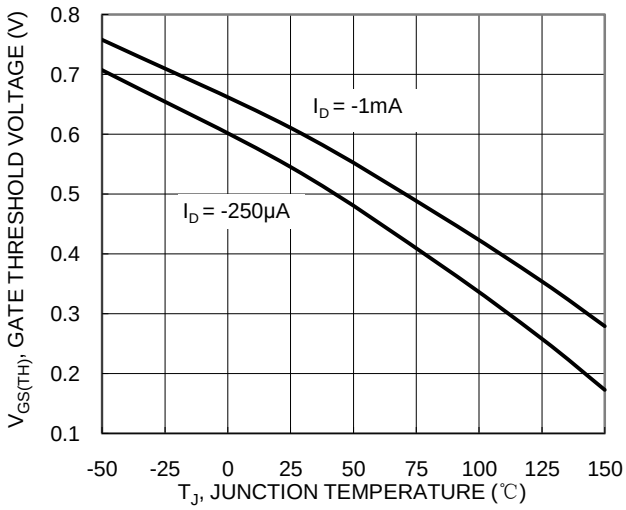


Figure 8. Gate Threshold Variation vs. Temperature

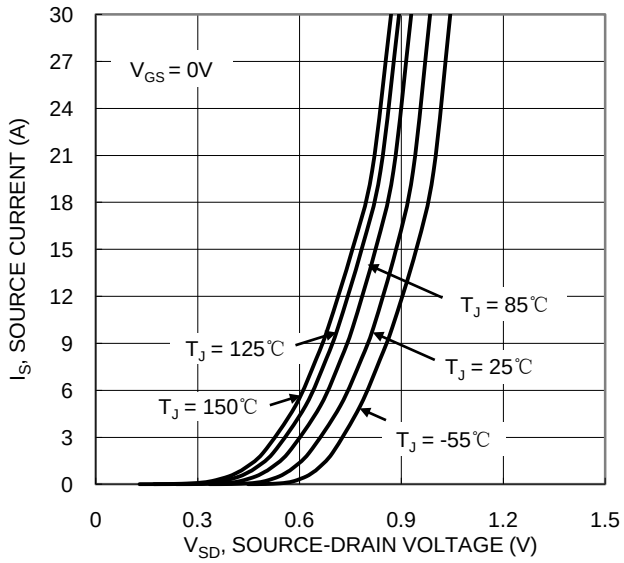


Figure 9. Diode Forward Voltage vs. Current

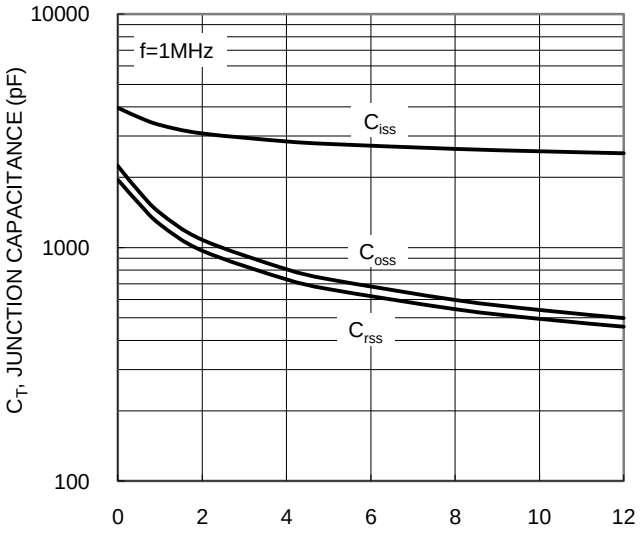


Figure 10. Typical Junction Capacitance

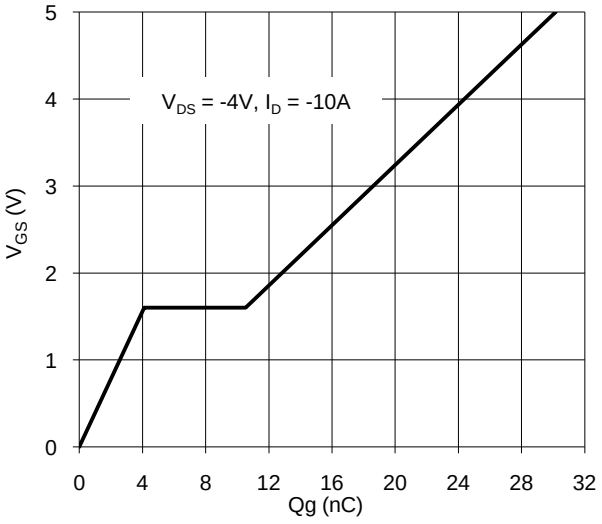


Figure 11. Gate Charge

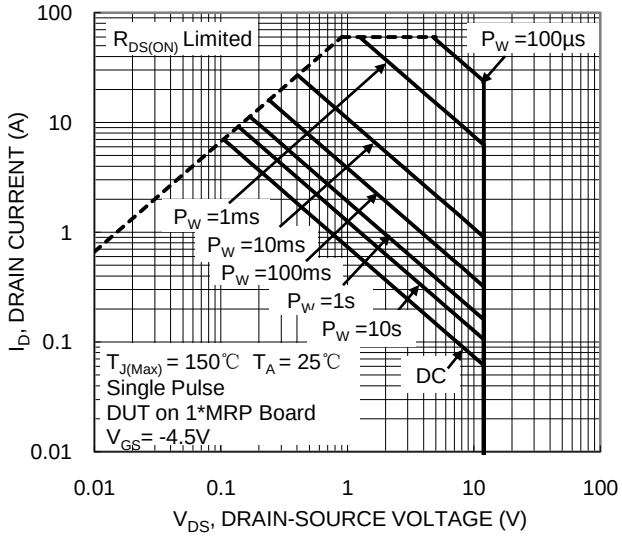


Figure 12. SOA, Safe Operation Area

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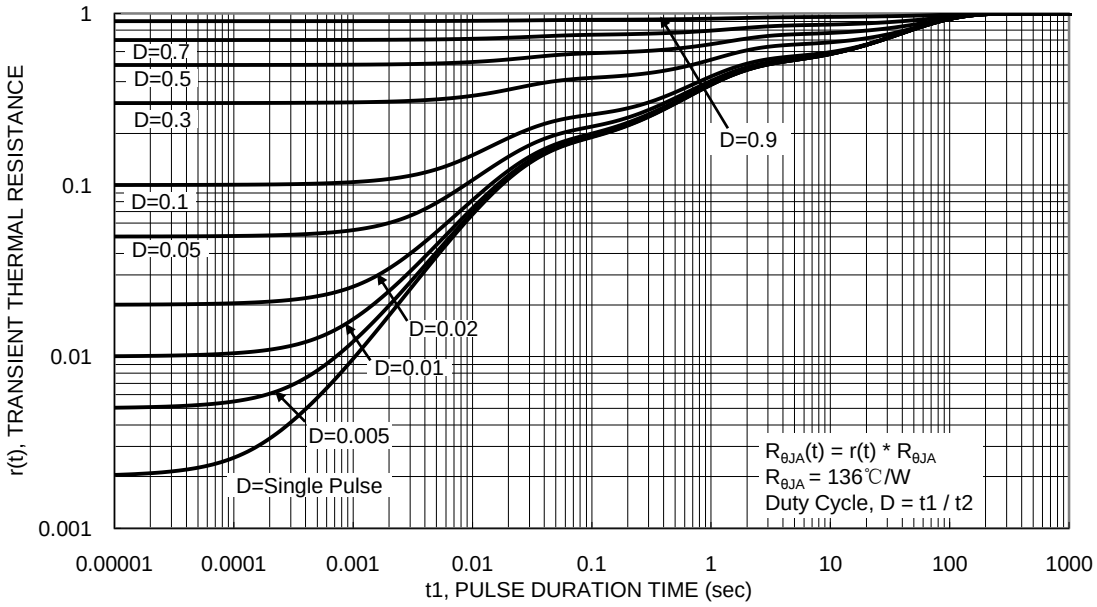


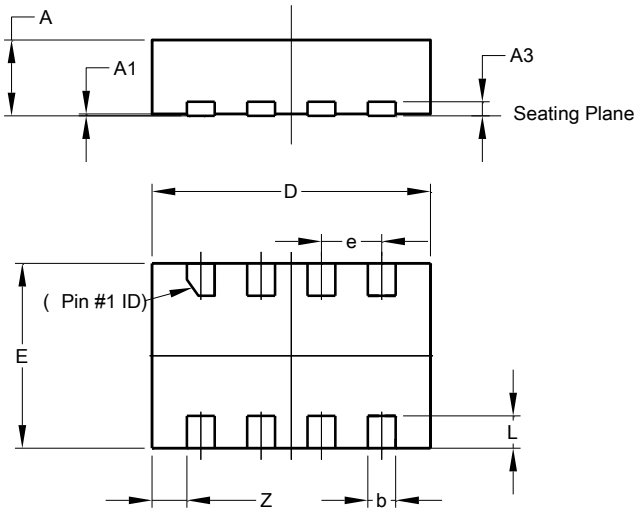
Figure 13. Transient Thermal Resistance

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

V-DFN3020-8

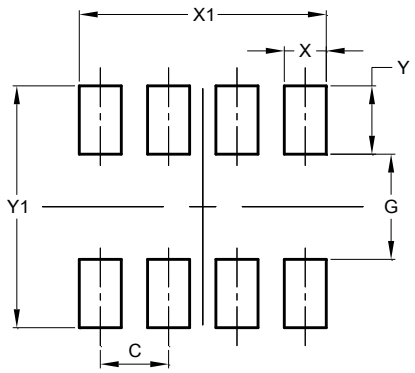


V-DFN3020-8			
Dim	**Min**	**Max**	**Typ**
A	0.77	0.83	0.80
A1	0	0.05	0.02
A3	-	-	0.203
b	0.25	0.35	0.30
D	2.95	3.05	3.00
e	-	-	0.65
E	1.95	2.05	2.00
L	0.30	0.40	0.35
Z	-	-	0.375
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

V-DFN3020-8



Dimensions	Value (in mm)
C	0.650
G	1.000
X	0.400
X1	2.350
Y	0.650
Y1	2.300

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